

## **SGN3025V**

#### 30V N-CHANNEL POWER MOSFET

**V**<sub>DSS</sub> , **30V** 

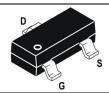
 $R_{\text{DS(ON)}}$  ,  $26m\Omega$  (max.) @  $V_{\text{GS}}{=}10V$ 

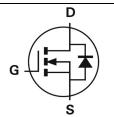
 $R_{\text{DS(ON)}}$  ,  $31m\Omega$  (max.) @  $V_{\text{GS}}{=}4.5V$ 

 $R_{DS(ON)}$ , 39m $\Omega$  (max.) @  $V_{GS} = 2.5V$ 

 $I_D$ , 4.8A







#### **Description**

The SGN3025V uses advanced Trench technology and designs to provide excellent  $R_{\text{DS(ON)}}$  with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

#### **Features**

- Low On-Resistance
- Low Input Capacitance
- · Low Miller Charge
- Low Input/Output Leakage

#### **Applications**

- Motor / Body Load Control
- · Automotive Systems
- Load Switch
- DC-DC converters and Off-line UPS

**Ordering Information** 

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SGN3025V	Halogen-Free	S0T-23S	V	Tape & Reel	3,000

#### Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Param	eter	Symbol	Value	Unit
Drain-Source Voltage		$V_{ m DS}$	30	٧
Gate-Source Voltage		$V_{GS}$	±12	٧
Drain Current-Continuous	T <sub>A</sub> =25°C		4.8	Α
Drain Current-Continuous	T <sub>A</sub> =70°C	ID	3.8	Α
Drain Current-Pulsed Note 1		I <sub>DM</sub>	20	Α
Maximum Dawar Dissipation	T <sub>A</sub> =25°C	D	1	W
Maximum Power Dissipation	T <sub>A</sub> =70°C	$ P_{D}$	0.6	W
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C
Operating Junction Temperature Range		T <sub>J</sub>	-55 to +150	°C

#### **Thermal Resistance Ratings**

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 2	$R_{\theta_{JA}}$	Steady State	-	-	125	°C/W
Maximum Junction-to-Case Note 2	$R_{\Theta JC}$	Steady State	-	-	80	°C/W

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# SGN3025V

#### 30V N-CHANNEL POWER MOSFET

#### Electrical Characteristics (T<sub>1</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_{DS} = 250 \mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}=24V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage	I <sub>GSS</sub>	$V_{GS} = \pm 12V, V_{DS} = 0V$	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	0.5	0.7	1.2	V
		$V_{GS}=10V$ , $I_{DS}=4A$	-	24	26	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =4.5V, $I_{DS}$ =3A	-	25	31	mΩ
		$V_{GS}=2.5V$ , $I_{DS}=2A$	-	29	39	

DYNAMIC CHARACTERISTICS							
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Input Capacitance	C <sub>iss</sub>		-	636	-		
Output Capacitance	$C_{oss}$	$V_{DS}=15V$ , $V_{GS}=0V$ , $f=1MHz$	-	50	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	43	-		

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	$T_{d(on)}$		-	3.3	-	
Rise Time	t <sub>r</sub>	$V_{DD} = 15V$ , $V_{GS} = 4.5V$ , $R_G = 3.3\Omega$ , $I_D = 3A$	-	41.2	-	ns
Turn-Off Delay Time	$T_{d(off)}$		-	21.5	-	
Fall Time	t <sub>f</sub>		-	6.2	-	
Total Gate Charge	$Q_{\rm g}$		-	8.2	-	
Gate to Source Gate Charge	$Q_{gs}$	$V_{DS} = 15V$ , $I_{DS} = 3A$ , $V_{GS} = 4.5V$	-	1.3	-	nC
Gate to Drain "Miller" Charge	$Q_{\mathrm{gd}}$		-	1.9	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous Source Current Note 2, 3	I <sub>s</sub>	V V OV F O	-	-	4.5	А
Pulsed Source Current Note 1, 3	I <sub>SM</sub>	$V_{\rm G} = V_{\rm D} = 0V$ , Force Current	-	-	18	Α
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V$ , $I_S=4A$	-	-	1.3	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	1 44 41/44 1004/	-	6.6	-	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$I_F$ =4A, dl/dt=100A/ $\mu$ s,	-	2.2	-	nC

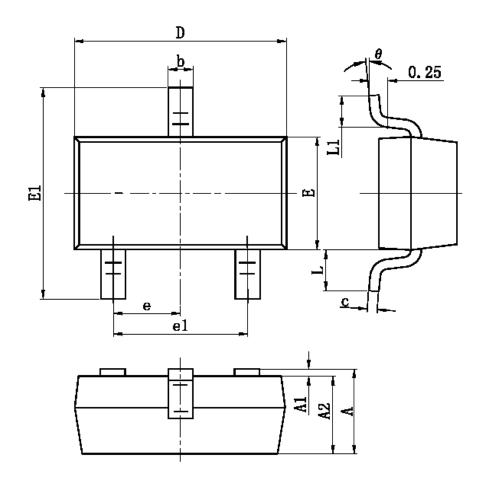
#### Notes:

- 1. Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2\%$ .
- 2. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BJC</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design. R<sub>BJA</sub> shown below for single device operation on FR-4 in still air.
- 3. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.





### **Package Dimensions**

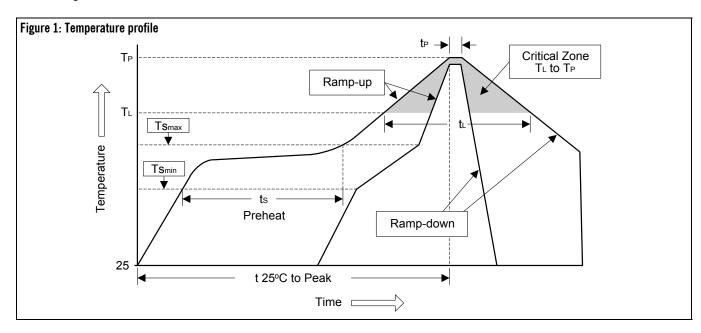


	Dimensions					
	Millimeters					
Symbols	Min.	Тур.	Max.	Min.	Тур.	Max.
A	0.90	1.03	1.15	0.035	0.040	0.045
A1	0.00	0.08	0.15	0.000	0.003	0.006
A2	0.90	0.50	0.11	0.035	0.020	0.004
b	0.30	0.40	0.50	0.012	0.016	0.020
С	0.08	0.12	0.15	0.003	0.005	0.006
D	2.80	2.90	3.00	0.110	0.114	0.118
E	1.20	1.30	1.40	0.047	0.051	0.055
E1	2.25	2.40	2.55	0.089	0.094	0.100
е		0.95			0.037	
e1	1.80	1.90	2.00	0.071	0.075	0.079
L		0.55			0.022	
L1	0.20	0.35	0.50	0.008	0.014	0.020
θ	0°	<b>4</b> °	9°	0°	4°	9°



### **Soldering Methods for Silicongear's Products**

- 1. Storage environment: Temperature =  $10^{\circ}$ C to  $35^{\circ}$ C Humidity =  $65\% \pm 15\%$
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate ( $T_L$ to $T_P$ )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T <sub>L</sub>		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t <sub>P</sub> )	10 to 30 300	20 to 40 300
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec





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